

Logic

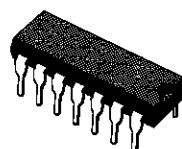
Order code	Manufacturer code	Description
83-0264	HCF4011BM1	4011BM NAND GATE (RC)
83-0274	HCF4023BM1	4023BM TRIPLE 3-INPUT NAND GATE
83-0328	HCF4011BEY	4011B QUAD 2 INPUT NAND GATE (RC)
83-0330	HCF4012BEY	4012B QUAD 4-INPUT NAND GATE
83-0352	HCF4023BEY	4023B TRIPLE 3 INPUT NAND (SEE 83-0353)

Logic	Page 1 of 12
The enclosed information is believed to be correct, Information may change without notice due to product improvement. Users should ensure that the product is suitable for their use. E. & O. E.	Revision A 20/02/2007

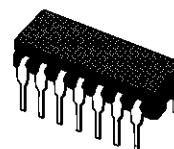
NAND GATES

QUAD 2 INPUT HCC/HCF 4011B
DUAL 4 INPUT HCC/HCF 4012B
TRIPLE 3 INPUT HCC/HCF 4023B

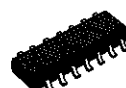
- PROPAGATION DELAY TIME = 60ns (typ.) AT $C_L = 50\text{pF}$, $V_{DD} = 10\text{V}$
- BUFFERED INPUTS AND OUTPUTS
- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- 5V, 10V AND 15V PARAMETRIC RATINGS
- MEETS ALL REQUIREMENTS OF JEDEC TENTATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"



EY
(Plastic Package)



F
(Ceramic Frit Seal Package)



M1
(Micro Package)



C1
(Plastic Chip Carrier)

ORDER CODES:

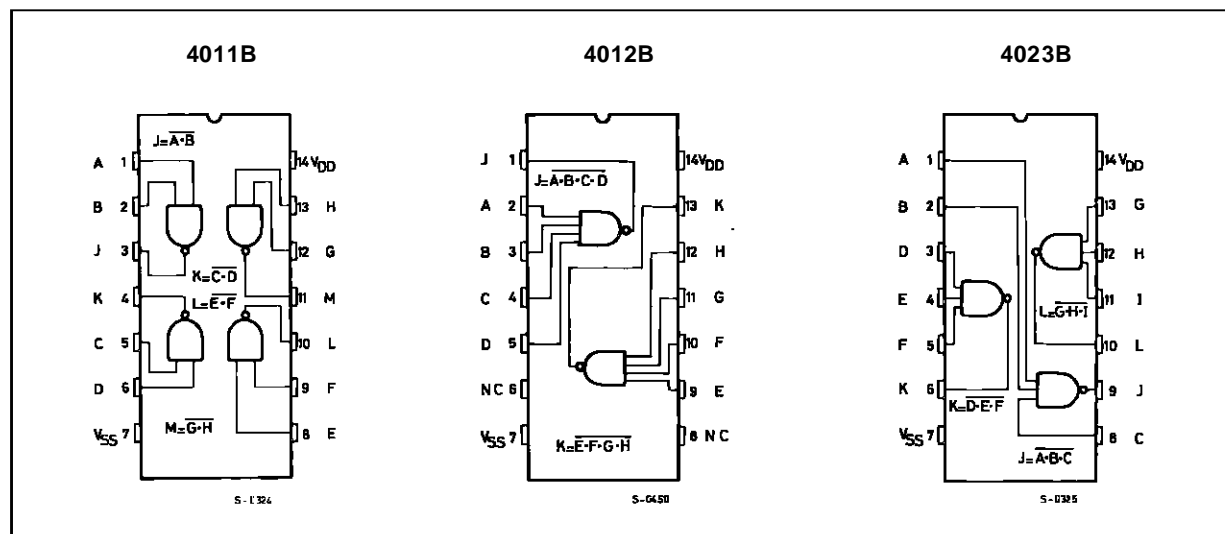
HCC40XXBF HCF40XXBM1
HCF40XXBEY HCF40XXBC1

DESCRIPTION

The **HCC4011B**, **HCC4012B** and **HCC4023B** (extended temperature range) and **HCF4011B**, **HCF4012B** and **HCF4023B** (intermediate temperature range) are monolithic, integrated circuit, available in 14-lead dual in-line plastic or ceramic package and plastic micropackage.

The **HCC/HCF4011B**, **HCC/HCF4012B** and **HCC/HCF4023B** NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of COS/MOS gates. All inputs and outputs are buffered.

PIN CONNECTIONS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}^*	Supply Voltage : HCC Types HCF Types	– 0.5 to + 20	V
		– 0.5 to + 18	V
V_i	Input Voltage	– 0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current (any one input)	± 10	mA
P_{tot}	Total Power Dissipation (per package) Dissipation per Output Transistor for T_{op} = Full Package-temperature Range	200	mW
		100	mW
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125	°C
		– 40 to + 85	°C
T_{stg}	Storage Temperature	– 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability.

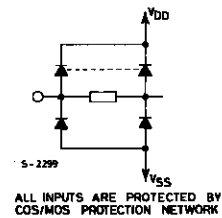
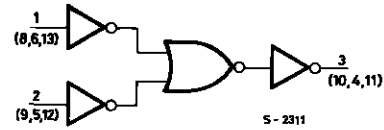
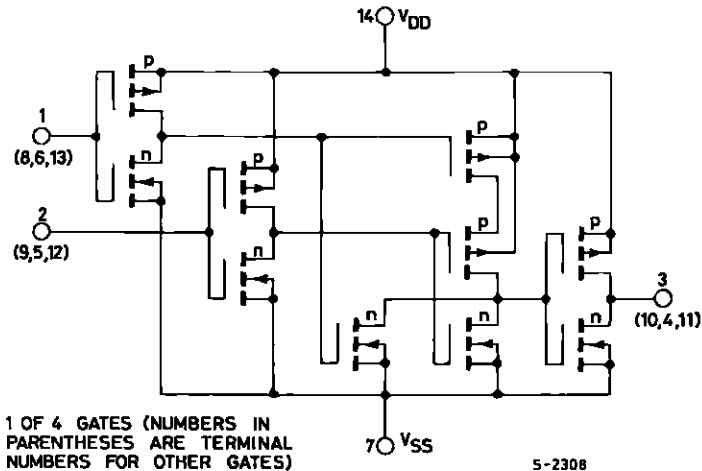
* All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

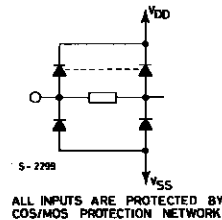
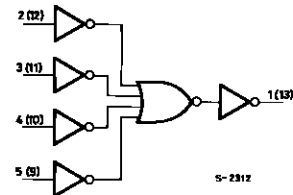
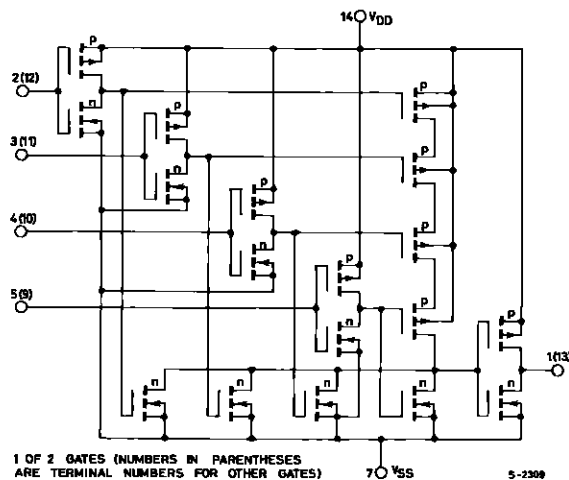
Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage : HCC Types HCF Types	3 to 18	V
		3 to 15	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature : HCC Types HCF Types	– 55 to + 125	°C
		– 40 to + 85	°C

SCHEMATIC AND LOGIC DIAGRAMS

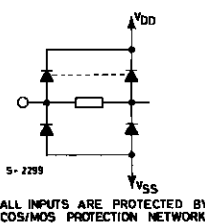
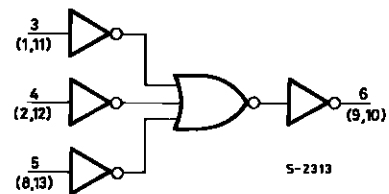
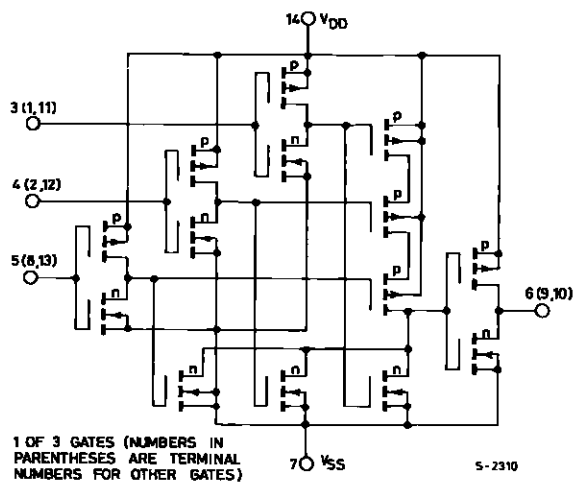
4011B



4012B



4023B



STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

Symbol	Parameter		Test Conditions				Value						Unit	
			V _I (V)	V _O (V)	I _O (μA)	V _{DD} (V)	T _{Low} *		25°C			T _{High} *		
							Min.	Max.	Min.	Typ.	Max.	Min.		Max.
I _L	Quiescent Current	HCC Types	0/5			5		0.25		0.01	0.25		7.5	μA
			0/10			10		0.5		0.01	0.5		15	
			0/15			15		1		0.01	1		30	
			0/20			20		5		0.02	5		150	
		HCF Types	0/ 5			5		1		0.01	1		7.5	
			0/10			10		2		0.01	2		15	
			0/15			15		4		0.01	4		30	
V _{OH}	Output High Voltage	0/5		< 1	5	4.95		4.95			4.95		V	
		0/10		< 1	10	9.95		9.95			9.95			
		0/15		< 1	15	14.95		14.95			14.95			
V _{OL}	Output Low Voltage	5/0		< 1	5		0.05			0.05		0.05	V	
		10/0		< 1	10		0.05			0.05		0.05		
		15/0		< 1	15		0.05			0.05		0.05		
V _{IH}	Input High Voltage		0.5/4.5	< 1	5	3.5		3.5			3.5		V	
			1/9	< 1	10	7		7			7			
			1.5/13.5	< 1	15	11		11			11			
V _{IL}	Input Low Voltage		4.5/0.5	< 1	5		1.5			1.5		1.5	V	
			9/1	< 1	10		3			3		3		
			13.5/1.5	< 1	15		4			4		4		
I _{OH}	Output Drive Current	HCC Types	0/5	2.5		5	− 2		− 1.6	− 3.2		− 1.15		mA
			0/5	4.6		5	− 0.64		− 0.51	− 1		− 0.36		
			0/10	9.5		10	− 1.6		− 1.3	− 2.6		− 0.9		
			0/15	13.5		15	− 4.2		− 3.4	− 6.8		− 2.4		
		HCF Types	0/5	2.5		5	− 1.53		− 1.36	− 3.2		− 1.1		
			0/5	4.6		5	− 0.52		− 0.44	− 1		− 0.36		
			0/10	9.5		10	− 1.3		− 1.1	− 2.6		− 0.9		
			0/15	13.5		15	− 3.6		− 3.0	− 6.8		− 2.4		
I _{OL}	Output Sink Current	HCC Types	0/5	0.4		5	0.64		0.51	1		0.36	mA	
			0/10	0.5		10	1.6		1.3	2.6		0.9		
			0/15	1.5		15	4.2		3.4	6.8		2.4		
		HCF Types	0/5	0.4		5	0.52		0.44	1		0.36		
			0/10	0.5		10	1.3		1.1	2.6		0.9		
			0/15	1.5		15	3.6		3.0	6.8		2.4		
I _{IH} , I _{IL}	Input Leakage Current	HCC Types	0/18	Any Input	18		± 0.1		±10 ^{−5}	± 0.1		± 1	μA	
		HCF Types	0/15		15		± 0.3		±10 ^{−5}	± 0.3		± 1		
C _I	Input Capacitance			Any Input					5	7.5			pF	

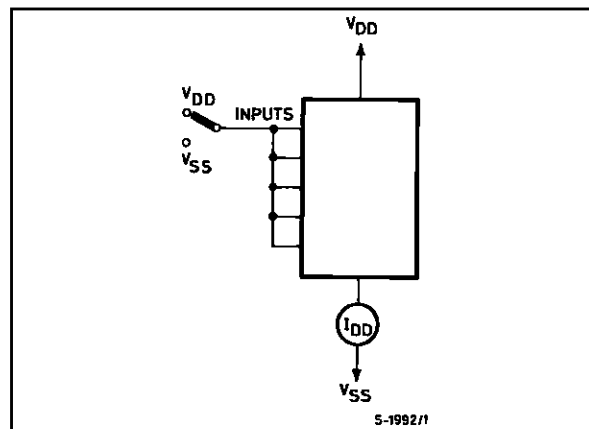
* T_{Low} = - 55°C for **HCC** device : - 40°C for **HCF** device.* T_{High} = + 125°C for **HCC** device : + 85°C for **HCF** device.The Noise Margin for both "1" and "0" level is : 1V min. with V_{DD} = 5V, 2V min. with V_{DD} = 10V, 2.5V with V_{DD} = 15V.

DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, $C_L = 50\text{pF}$, $R_L = 200\text{k}\Omega$, typical temperature coefficient for all V_{DD} values is $0.3\%/^{\circ}\text{C}$, all input rise and fall times = 20ns)

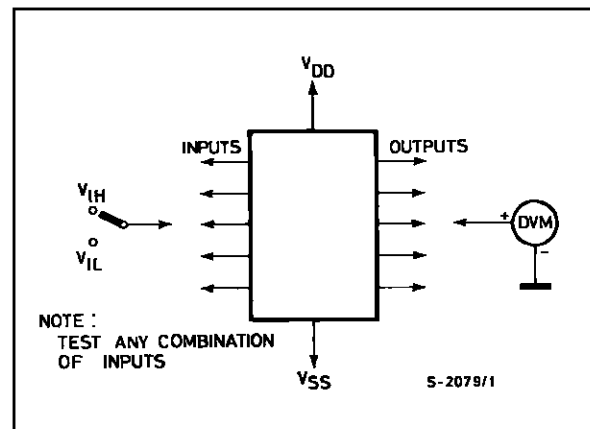
Symbol	Parameter	Test Conditions		Value			Unit
			V_{DD} (V)	Min.	Typ.	Max.	
t_{PLH} , t_{PHL}	Propagation Delay Time		5		125	250	ns
			10		60	120	
			15		45	90	
t_{THL} , t_{TLH}	Transition Time		5		100	200	ns
			10		50	100	
			15		40	80	

TEST CIRCUITS

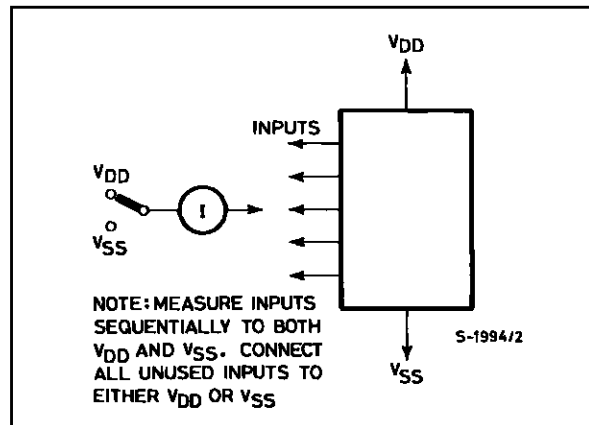
Quiescent Device Current



Noise Immunity.

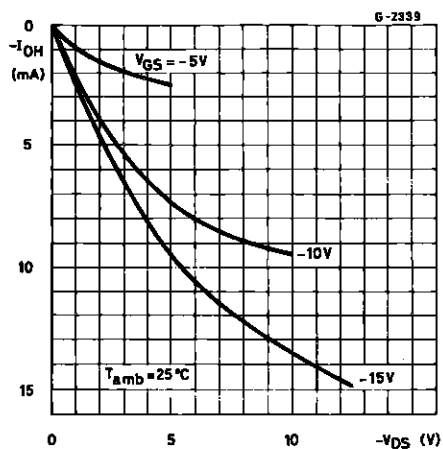


Input Leakage Current.

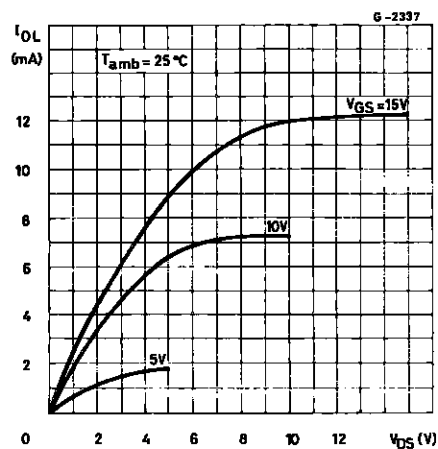


NOTE: MEASURE INPUTS
SEQUENTIALLY TO BOTH
 V_{DD} AND V_{SS} . CONNECT
ALL UNUSED INPUTS TO
EITHER V_{DD} OR V_{SS}

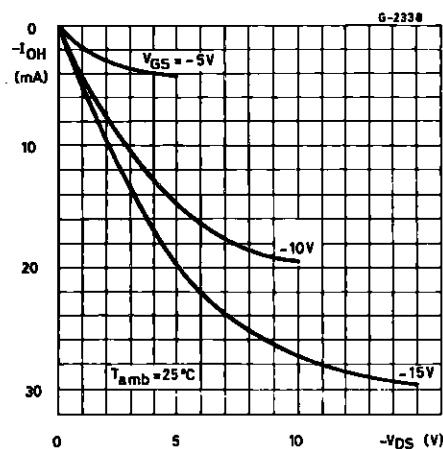
Minimum Output High (source) Current Characteristics.



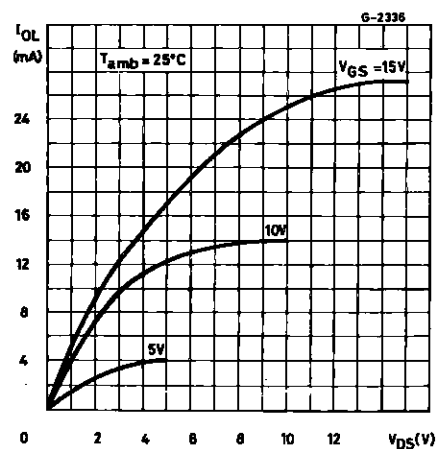
Minimum Output Low (sink) Current Characteristics.



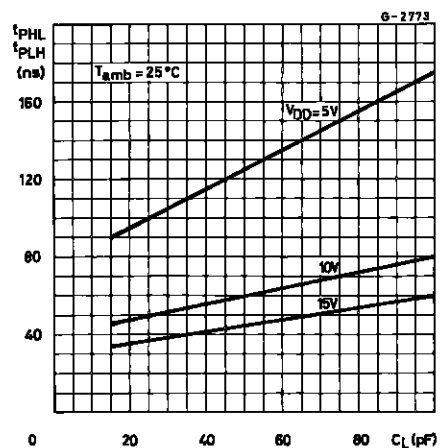
Typical Output High (source) Current Characteristics.



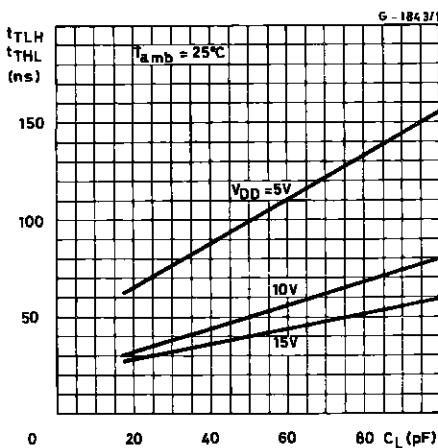
Typical Output Low (sink) Current Characteristics.



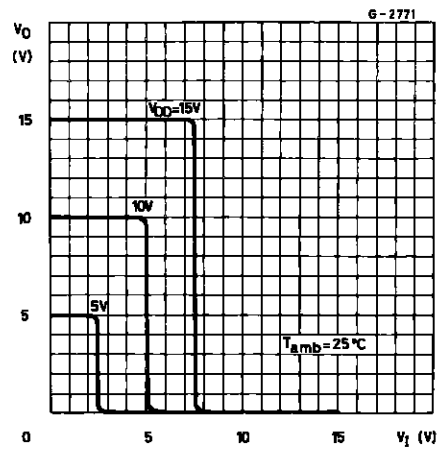
Typical Propagation Delay Time per Gate as a Function of Load Capacitance.



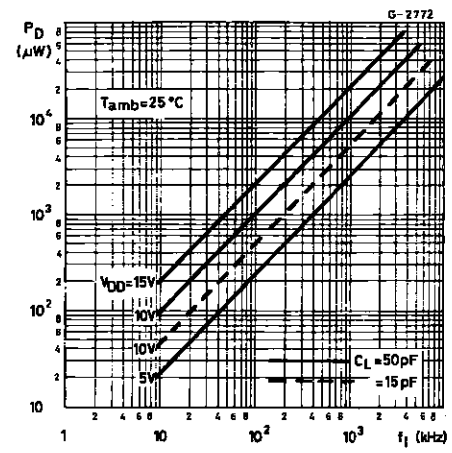
Typical Transition Time vs. Load Capacitance.



Typical Voltage Transfer Characteristics.

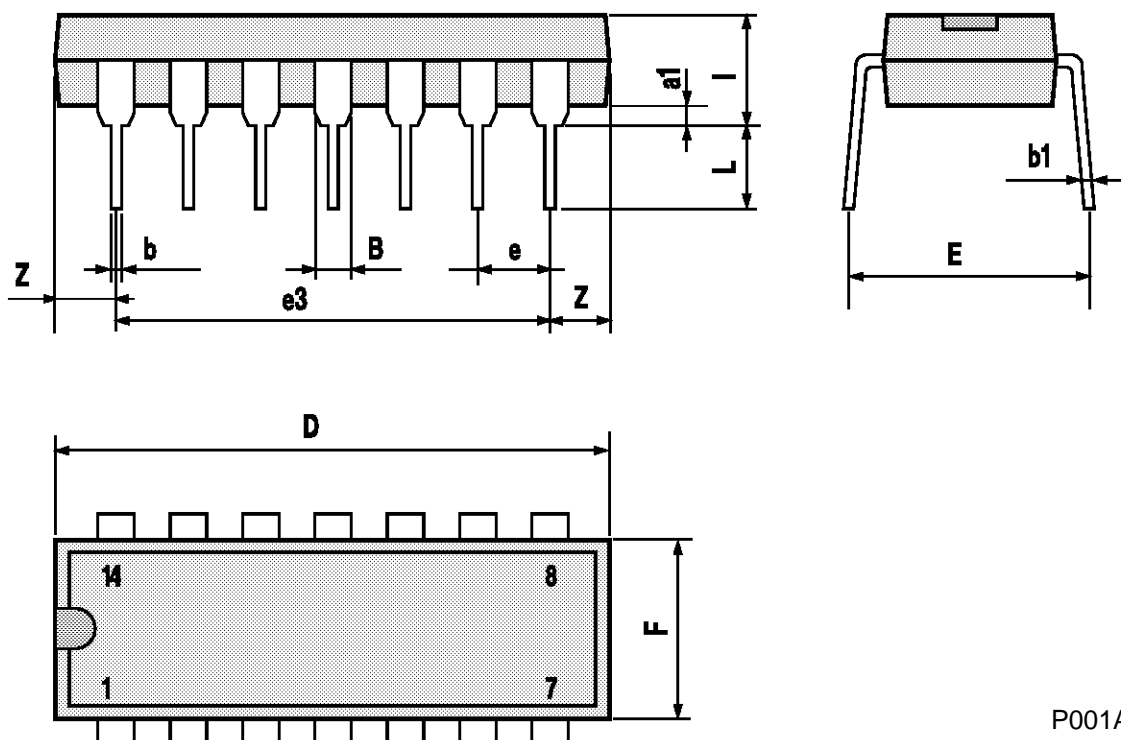


Typical Power Dissipation/gate vs Frequency.



Plastic DIP14 MECHANICAL DATA

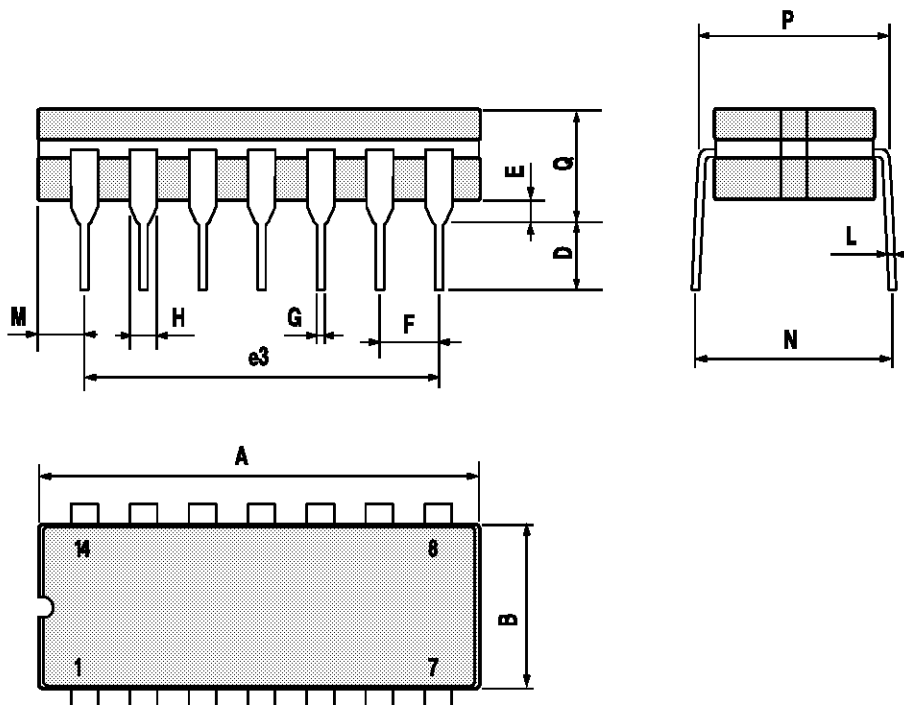
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

Ceramic DIP14/1 MECHANICAL DATA

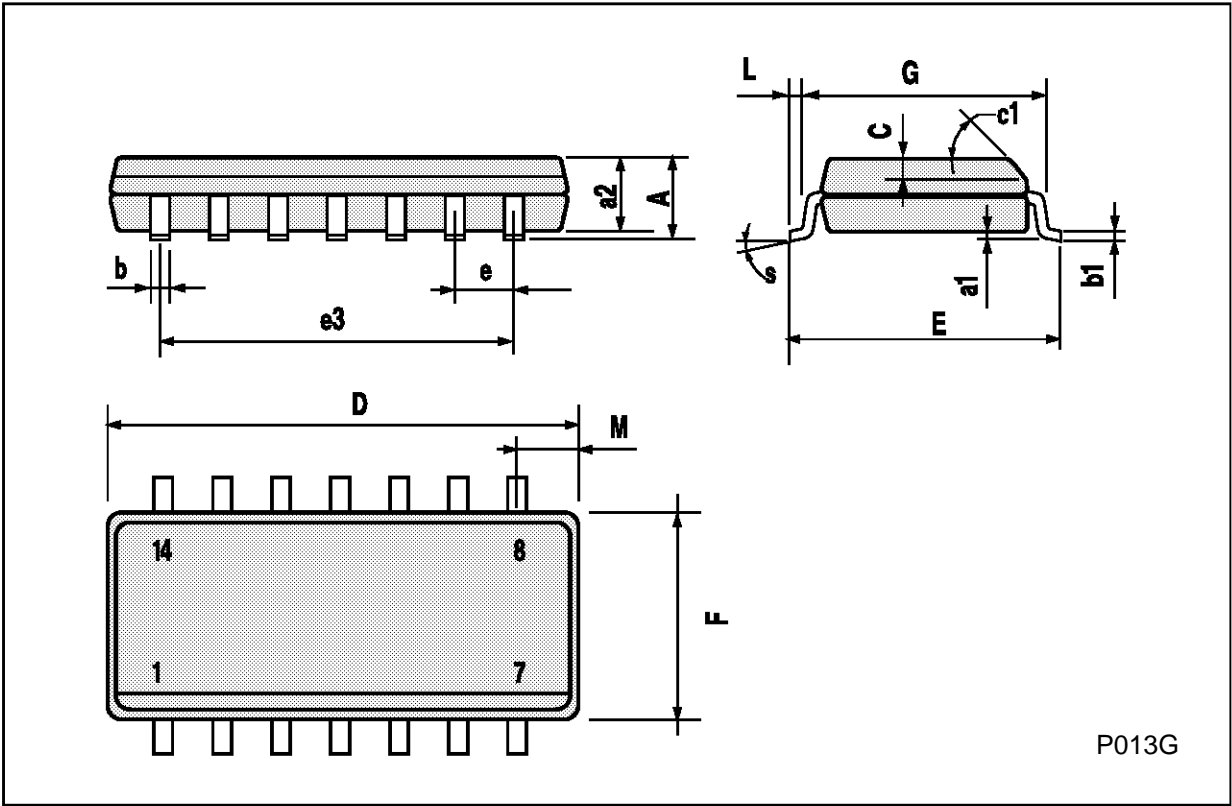
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

SO14 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	

